

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An electro-optical apparatus, comprising:
a pair of substrates;
an electro-optical material disposed between the pair of substrates;
a switching element disposed above one of said substrates; and
a light shielding film disposed at a location ~~opposing that opposes~~ said switching element, and that is on said one of said substrates, said light shielding film including:
a metal layer formed of a refractory metal in the form of a simple substance or a refractory metal compound; and
~~a barrier layer~~ barrier layers disposed on at least one surface of said metal layer, such that side faces of a lower barrier layer and side faces of the metal layer are covered with an upper barrier layer, said barrier ~~layers~~ layer being formed of a refractory metal or a refractory metal compound containing no oxygen.
- 2-3. (Canceled).
4. (Currently Amended) The electro-optical apparatus according to Claim 1, the metal layer of said light shielding film including a light shielding metal ~~layer~~ and a light-absorbable metal layer, ~~and said light absorbable metal layer being disposed on a side facing said switching element.~~
5. (Withdrawn) The electro-optical apparatus according to Claim 1, said metal layer being interposed between said barrier layers.
6. (Canceled).

7. (Original) The electro-optical apparatus according to Claim 1, said light shielding film being connected to a fixed potential.

8. (Currently Amended) The electro-optical apparatus according to Claim 1, said ~~light barrier-barriers~~ layer being formed of a material selected from the group including a nitride compound, a silicon compound, a tungsten compound, tungsten, and silicon.

9. (Currently Amended) The electro-optical apparatus according to Claim 1, said barrier ~~layer-layers~~ being formed of WSi.

10. (Original) The electro-optical apparatus according to Claim 9, said metal layer being formed of Ti.

11. (Withdrawn) The electro-optical apparatus according to Claim 10, said barrier layer being formed on upper and lower surfaces of said metal layer, such that a thickness of the barrier layer formed on the upper surface is greater than a thickness on the lower surface.

12. (Withdrawn) The electro-optical apparatus according to Claim 11, the thickness of said metal layer being within the range from 30 nm to 50 nm, the thickness of the upper barrier layer being within the range from 30 nm to 100 nm, and the thickness of the lower barrier layer being within the range from 10 nm to 20 nm.

13. (Withdrawn) An electronic device, comprising:
the electro-optical apparatus according to Claim 1.

14-15. (Canceled).

16. (Currently Amended) The method of producing a substrate for use in an electro-optical apparatus according to Claim 15, further comprising:

forming a barrier layer by depositing a film of a refractory metal or a refractory metal compound containing no oxygen ~~upon said metal layer~~ prior to forming the metal layer.

17. (Previously Presented) The method of producing a substrate for use in an electro-optical apparatus according to Claim 15, said forming the insulating film including performing heat treatment at a temperature in the range from 500°C to 1100°C.
18. (Canceled).
19. (Withdrawn) The light shielding film according to Claim 18, said barrier layer being formed of a material selected from the group including a nitride compound, a silicon compound, a tungsten compound, tungsten, and silicon.
20. (Withdrawn) The light shielding film according to Claim 19, said barrier layer being formed of a nitride compound selected from the group including SiN, TiN, WN, MoN, and CrN.
21. (Withdrawn) The light shielding film according to Claim 19, said barrier layer being formed of a silicon compound selected from the group including TiSi, WSi, MoSi, CoSi, and CoSi.
22. (Withdrawn) The light shielding film according to Claim 19, said barrier layer being formed of a tungsten compound selected from the group including TiW and MoW.
23. (Withdrawn) The light shielding film according to Claim 18, said metal layer being formed of a simple substance of metal selected from the group including Ti, W, Mo, Co, Cr, Hf, and Ru.
24. (Withdrawn) The light shielding film according to Claim 18, said metal layer being formed of a metal compound selected from the group including TiN, TiW, and MoW.
25. (Withdrawn) The light shielding film according to Claim 18, the thickness of said barrier layer being within the range from 1 to 200 nm.
26. (Withdrawn) The light shielding film according to Claim 18, the thickness of said metal layer being within the range from 10 to 200 nm.

27. (Withdrawn) The light shielding film according to Claim 18, said barrier layers being formed on both surfaces of said metal layer into a multilayer structure.
28. (Withdrawn) The light shielding film according to Claim 18, said metal layer including a light-reflective metal layer and a light-absorbable metal layer.
29. (Withdrawn) The light shielding film according to Claim 28, said light-absorbable metal layer being formed of a nitride compound.
30. (Withdrawn) The light shielding film according to Claim 28, said metal layer including a light-shielding metal layer and light-absorbable metal layers disposed on two respective opposing surfaces of said light-shielding metal layer.
31. (Withdrawn) A light shielding film, comprising:
a metal layer formed of a refractory metal in the form of a simple substance or a refractory metal compound; and
a protection layer formed of a refractory metal or a refractory metal compound which is disposed on at least one surface of said metal layer so as to protect said metal layer from oxidation.
32. (Canceled).
33. (Currently Amended) The electro-optical apparatus according to ~~claim 19~~claim 1, ~~and said barrier layers being formed of tungsten.~~
34. (Previously Presented) An electro-optical apparatus, comprising:
a pair of substrates;
an electro-optical material disposed between the pair of substrates;
a switching element disposed above one of the substrates;
a light shielding film disposed at a location opposing the switching element;
and

an insulating film between the light shielding film and the switching element,
the light shielding film including:

a metal layer formed of a refractory metal in the form of a simple
substance or a refractory metal compound; and

barrier layers disposed on upper and lower surfaces of the metal layer,
the barrier layers being formed of a refractory metal or a refractory metal compound
containing no oxygen, the thickness of the barrier layer formed on the upper surface of the
metal layer being greater than a thickness of the barrier layer formed on the lower surface of
the metal layer.